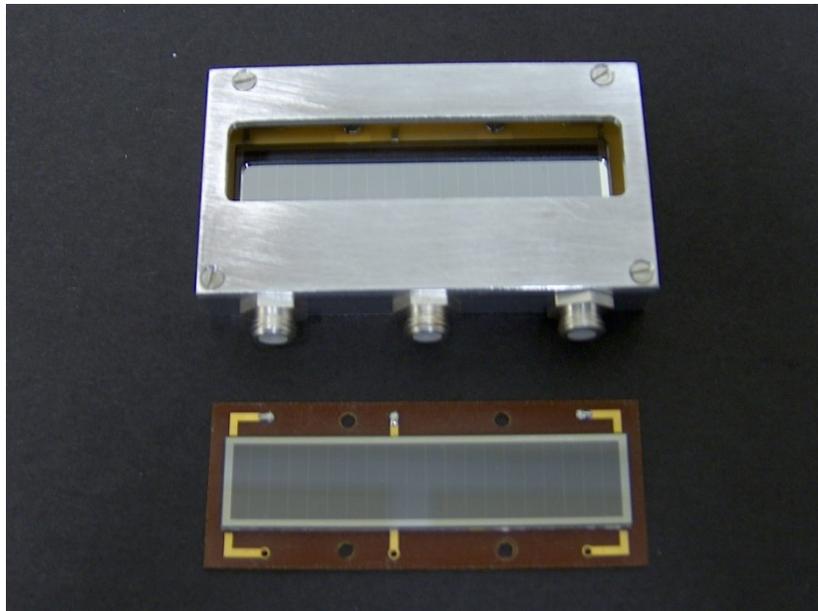


**SPECIALIST DETECTORS FOR NUCLEAR PHYSICS**

SILICON DETECTOR TYPE:	TOTALLY DEPLETED PLANAR STRUCTURE
DESIGN:	Silicon planar ion implanted structure p on n silicon totally depleted with resistive p junction layer featuring high uniformity and equipotential channel along the linear axis between the two anodes of this common cathode device.
TECHNOLOGY:	4 INCH SILICON
JUNCTION WINDOW:	PSD
OHMIC WINDOW:	2M
POSITION SENSITIVE:	1 axis
N <sup>o</sup> of DETECTORS:	1 or 2
ACTIVE AREA:	50 x 10 mm <sup>2</sup>
CAPITANCE (FD):	40-20 pF/cm subject to depletion depth
INTER ANODE RESISTANCE:	4 k $\Omega$ minimum – 10 k $\Omega$ maximum
ENTRANCE/EXIT WINDOW:	0.2 $\mu$ m
THICKNESS:	35 $\mu$ m, 65 $\mu$ m, 140 $\mu$ m, 300 $\mu$ m, 500 $\mu$ m and 1000 $\mu$ m
ALPHA RESOLUTION:	0.5 %
POSITON RESOLUTION:	100 $\mu$ m - 300 $\mu$ m subject to readout electronics.
OPERATING VOLTAGE:	10 – 250 V subject to thickness chosen
PACKAGES:	Single or double detector PCB available with metal frame. Detector assembly also available in a UHV package design.
CONNECTORS:	Conhex / 3 per detector unless PCB only



**Design T PSD/2M single PCB assembly and metal frame assembly.**

NOTE: See also Design TT Series, position sensitive detectors (PSD) 18 x 10 mm<sup>2</sup>.

QUALITY ASSURANCE: ISO9001